

IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~strikethrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please CANCEL claims 35-37 and AMEND claims 17 and 18 in accordance with the following:

1-12 (cancelled)

13. (previously amended) A capacitor comprising a first conducting film formed on a substrate, a first dielectric film formed on the first conducting film, a second conducting film formed on the first dielectric film, a second dielectric film formed above the second conducting film, covering an edge of the second conducting film, and a third conducting film formed above the second dielectric film, covering a part of the second dielectric film covering the edge of the second conducting film,

the capacitor further comprising:

an insulation film covering said edge of the second conducting film or said part of the second dielectric film,

wherein the insulation film is formed of an inorganic substance.

14. (cancelled)

15. (cancelled)

16. (original) A semiconductor device comprising a capacitor, the capacitor comprising a first conducting film formed on a substrate, a first dielectric film formed on the first conducting film, a second conducting film formed on the first dielectric film, a second dielectric film formed above the second conducting film, covering an edge of the second conducting film, and a third conducting film formed above the second dielectric film, covering a part of the second dielectric film covering the edge of the second conducting film,

the capacitor further comprising:

an insulation film covering said edge of the second conducting film or said part of the

second dielectric film.

17. (currently amended) A semiconductor device comprising:
a semiconductor element substrate;
a passive component mounted on the semiconductor element substrate and electrically connected to electrodes of the semiconductor element substrate;
column-shaped conductors formed ~~on~~over the semiconductor element substrate in a region other than a region where the passive component is mounted, and having a height which is substantially flush with at least the upper surface of the passive component, and
an insulation layer burying the passive component and the column-shaped conductors, the upper surfaces of the column-shaped conductors being exposed on the surface of the insulation film.

18. (currently amended) A semiconductor device comprising:
a semiconductor element substrate;
a passive component mounted on the semiconductor element substrate and electrically connected to electrodes of the semiconductor element substrate;
column-shaped conductors formed ~~on~~over the semiconductor element substrate in a region other than a region where the passive component is mounted; and
an insulation layer burying the passive component and the column-shaped conductors, the semiconductor element substrate being electrically connected to an outside terminal via the column-shaped conductors.

19. (original) A semiconductor device according to claim 17, wherein
the passive component includes a passive element formed on a side of a support substrate opposed to the semiconductor element substrate, and
the passive component includes electrodes electrically connected to the passive element and exposed on the side of the upper side of the support substrate.

20. (original) A semiconductor device according to claim 19, wherein
the electrodes exposed on the side of the upper surface of the support substrate are electrically connected to the passive element through the support substrate.

21. (original) A semiconductor device according to claim 17, wherein

a pitch of a plurality of the electrodes of the semiconductor element substrate is smaller than a pitch of a plurality of the column-shaped conductors.

22. (original) A semiconductor device according to claim 19, wherein the passive component further comprises through-electrodes insulated from the passive element and electrically connected to the semiconductor element substrate through the passive component.

23. (original) A semiconductor device according to claim 17, wherein the upper surface of the passive component is covered with the insulation layer.

24. (original) A semiconductor device comprising a semiconductor element substrate, and a passive component mounted on the semiconductor element substrate and electrically connected to electrodes of the semiconductor element substrate,

the passive component including a passive element formed on a side of a support substrate opposed to the semiconductor element substrate, and

the passive component including electrodes electrically connected to the passive element through the support substrate and exposed on the upper surface of the support substrate, and through-electrodes electrically connected to the semiconductor element substrate through the passive component and insulated from the passive element.

25. (original) A semiconductor device comprising a semiconductor element substrate, and a passive component including a passive element mounted on the semiconductor element substrate and electrically connected to electrodes of the semiconductor element substrate,

the passive component including electrodes electrically connected to the passive element and exposed on the upper surface of the passive component, and through-electrodes electrically connected to the semiconductor element substrate through the passive component and insulated from the passive element.

26. (original) A semiconductor device according to claim 22, further comprising: a wiring layer formed on the semiconductor element substrate and having relay wiring, the passive element, the column-shaped conductors or the through-electrodes are electrically connected to the semiconductor element substrate via the relay wiring.

27. (original) A semiconductor device according to claim 24, further comprising:
a wiring layer formed on the semiconductor element substrate and having relay wiring,
the passive element, the column-shaped conductors or the through-electrodes are
electrically connected to the semiconductor element substrate via the relay wiring.

28. (original) A semiconductor device according to claim 25, further comprising:
a wiring layer formed on the semiconductor element substrate and having relay wiring,
the passive element, the column-shaped conductors or the through-electrodes are
electrically connected to the semiconductor element substrate via the relay wiring.

29. (original) A semiconductor device according to claim 17, wherein
the passive component is flip chip-bonded to the electrodes of the semiconductor
element substrate or the electrodes formed on the wiring layer.

30. (original) A semiconductor device according to claim 24, wherein
the passive component is flip chip-bonded to the electrodes of the semiconductor
element substrate or the electrodes formed on the wiring layer.

31. (original) A semiconductor device according to claim 25, wherein
the passive component is flip chip-bonded to the electrodes of the semiconductor
element substrate or the electrodes formed on the wiring layer.

32. (original) A semiconductor device according to claim 17, wherein
the passive component is a capacitor, a resistor, or an inductor.

33. (original) A semiconductor device according to claim 24, wherein
the passive component is a capacitor, a resistor, or an inductor.

34. (original) A semiconductor device according to claim 25, wherein
the passive component is a capacitor, a resistor, or an inductor.

35-37. (cancelled)